

/ Descriptions

VRW5606 E SQS 1 Silicon PNP transistor in a SOT23-3 Plastic Package.

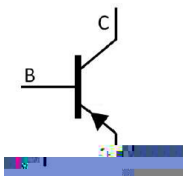
/ Features

High breakdown, low $V_{CE(sat)}$, complements the BR2SD1782MCQ, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

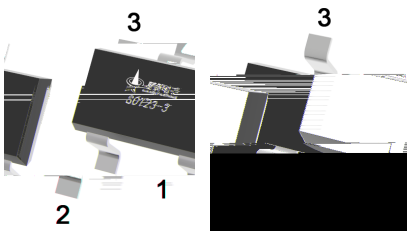
/ Applications

Medium power amplifier applications, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	Q	R
h_{FE} Range	120~270	180~390
Marking	QAKQ	QAKR

BR2SB1198MCQ

Rev.A Apr.-2023



DATA SHEET

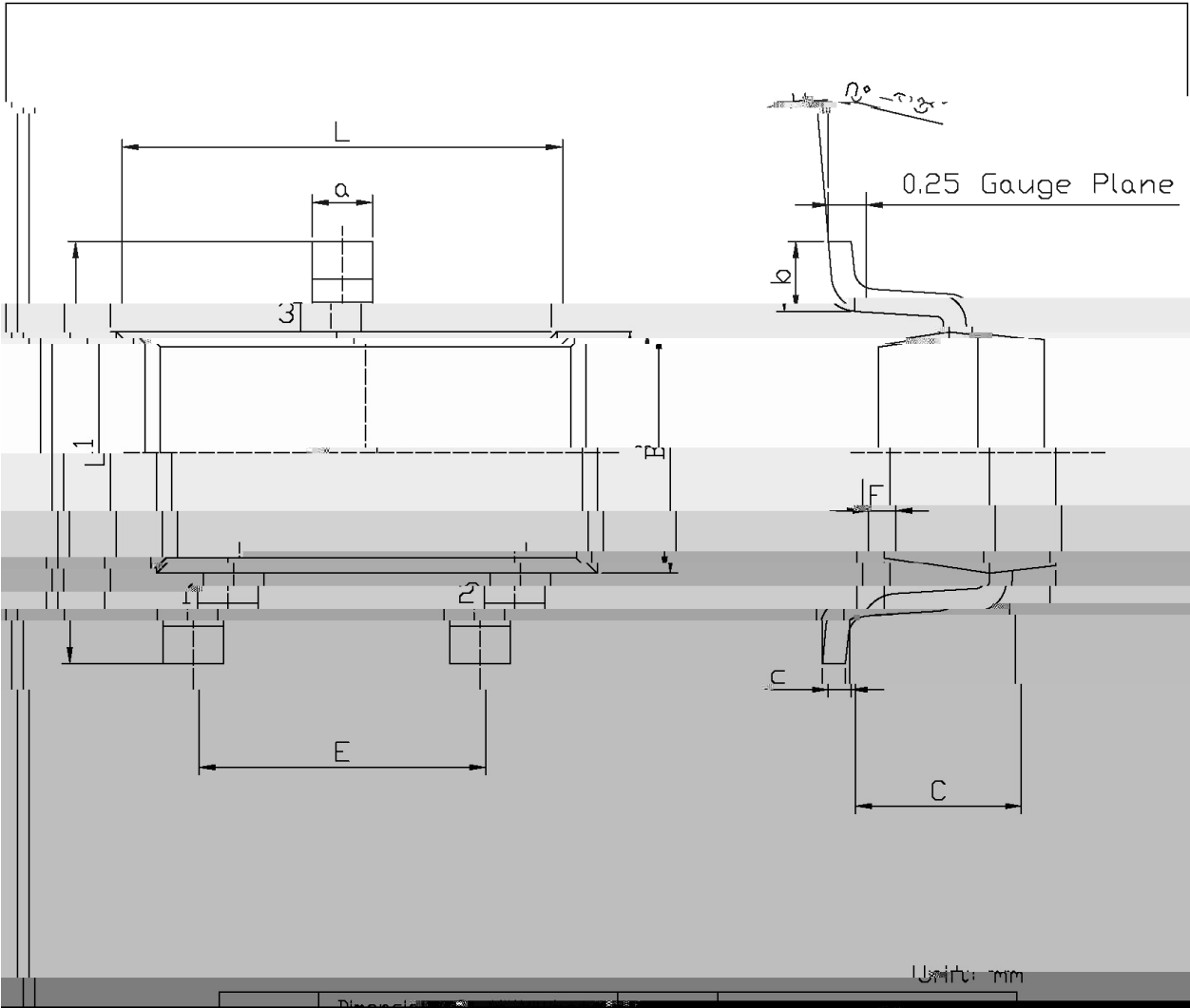
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-500	mA

BR2SB1198MCQ

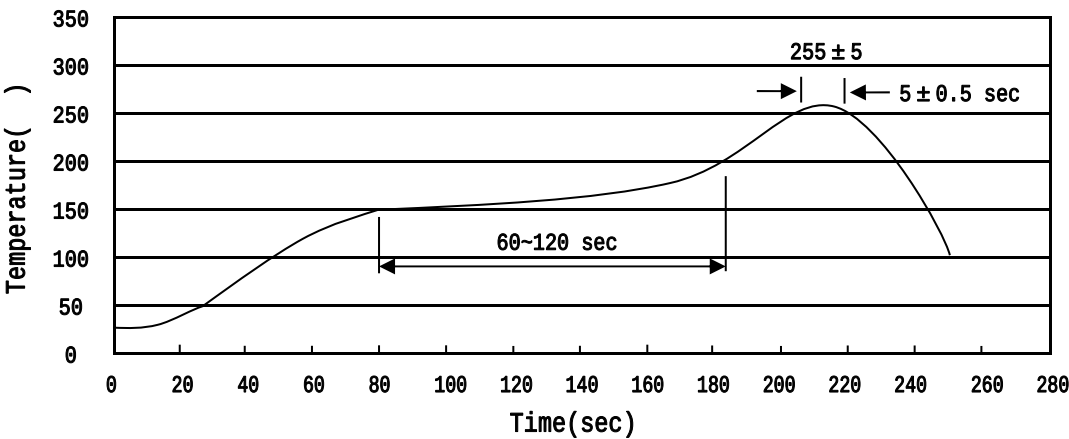
Rev.A Apr.-2023

DATA SHEET

/ Package Dimensions



() / Temperature Profile for IR Reflow Soldering(Pb-Free)



- Note:
1. Preheating: 150~200 °C, Time: 60~120sec.
2. Peak Temp.: 255±5 °C, Duration: 5±0.5sec.
3. Cooling Speed: 2~10 °C/sec.

/ Resistance to Soldering Heat Test Conditions

260±5 °C, 10±1 sec. Temp.: 260±5 °C Time: 10±1 sec

/ Packaging SPEC.

REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT23-3	3,000	10	30,000	4	120,000	7 × 8	210×205×205	445×230×435

/ Notices